Vishay Semiconductors

RoHS

COMPLIANT

HALOGEN FREE

# Thyristor, Surface Mount, Phase Control SCR, 16 A



PRIMARY CHARACTERISTICS						
I <sub>T(AV)</sub>	16 A					
$V_{DRM}/V_{RRM}$	800 V, 1200 V					
$V_{TM}$	1.25 V					
I <sub>GT</sub>	45 mA					
$T_J$	-40 to +125 °C					
Package	D <sup>2</sup> PAK (TO-263AB)					
Circuit configuration	Single SCR					

#### **FEATURES**

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **APPLICATIONS**

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

#### **DESCRIPTION**

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5							
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A						
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	16.5	25.0							

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I <sub>T(AV)</sub>	Sinusoidal waveform	16	۸					
I <sub>RMS</sub>		25	А					
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1200	V					
I <sub>TSM</sub>		350	A					
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V					
dV/dt		500	V/µs					
dl/dt		150	A/µs					
TJ		-40 to +125	°C					

VOLTAGE RATINGS			
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> , AT 125 °C mA
VS-25TTS08S-M3	800	800	10
VS-25TTS12S-M3	1200	1200	]



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ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEC	T CONDITIONS	VAL	UNITS				
PARAMETER	STINIBUL	STMBOL TEST CONDITIONS				UNITS			
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° c	onduction half sine wave	16					
Maximum RMS on-state current	I <sub>RMS</sub>			2	5	Α			
Maximum peak, one-cycle,	<b>I</b>	10 ms sine pulse, r	ated V <sub>RRM</sub> applied	30	00	_ A			
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, r	no voltage reapplied	35	50				
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	10 ms sine pulse, rated V <sub>RRM</sub> applied		45	50	A <sup>2</sup> s			
Maximum 1-t for fusing	1-1	10 ms sine pulse, r	no voltage reapplied	630		A-S			
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t	t = 0.1 ms to 10 ms	t = 0.1 ms to 10 ms, no voltage reapplied			A²√s			
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.25		V			
On-state slope resistance	r <sub>t</sub>	T <sub>.1</sub> = 125 °C		12	2.0	mΩ			
Threshold voltage	$V_{T(TO)} = 123 \text{ G}$			.0	V				
Maximum reverse and direct leakage current	1/1	T <sub>J</sub> = 25 °C	V <sub>B</sub> = rated V <sub>BBM</sub> /V <sub>DBM</sub>	0.	.5				
Maximum reverse and direct leakage current	I <sub>RM</sub> /I <sub>DM</sub>	T <sub>J</sub> = 125 °C	VR = rated VRRM/VDRM	1	0				
Holding current	I <sub>H</sub>	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $T_J = 25$ °C	-	150	mA			
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C			Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs			
Maximum rate of rise of turned-on current	dl/dt				150				

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	W	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA	
Maximum required DC gate current to trigger	I <sub>GT</sub>	Anode supply = 6 V, resistive load, $T_J = 25$ °C	45		
		Anode supply = 6 V, resistive load, $T_J$ = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0 V		
		Anode supply = 6 V, resistive load, $T_J = 125  ^{\circ}\text{C}$	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	T = 105 °C V = reted value	0.25		
Maximum DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = 125 °C, V <sub>DRM</sub> = rated value	2.0	mA	

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9						
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	4	μs					
Typical turn-off time	t <sub>q</sub>	T <sub>J</sub> = 125 °C	110						

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	VALUES	UNITS							
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C					
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	R <sub>thJC</sub> DC operation		°C/W					
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> <sup>(1)</sup>		40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	OZ.					
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TTS08S						
ivial killy device		Case style D-FAR (10-203AB)	25TTS12S						

#### Note

<sup>(1)</sup> When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

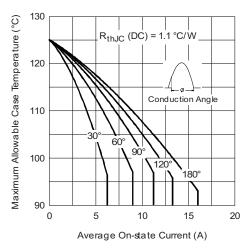


Fig. 1 - Current Rating Characteristics

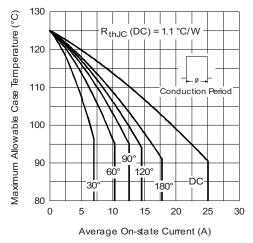


Fig. 2 - Current Rating Characteristics

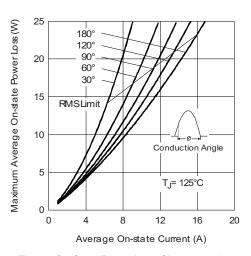


Fig. 3 - On-State Power Loss Characteristics

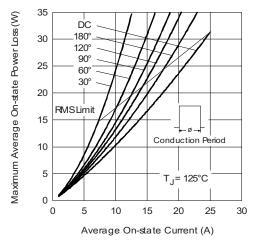


Fig. 4 - On-State Power Loss Characteristics

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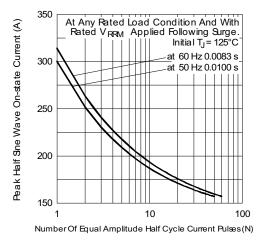


Fig. 5 - Maximum Non-Repetitive Surge Current

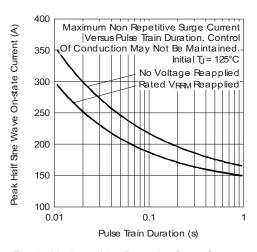


Fig. 6 - Maximum Non-Repetitive Surge Current

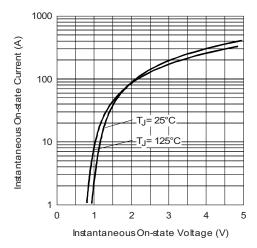


Fig. 7 - On-State Voltage Drop Characteristics

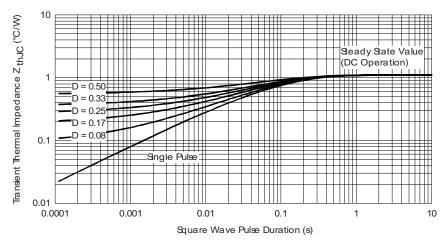


Fig. 8 - Gate Characteristics

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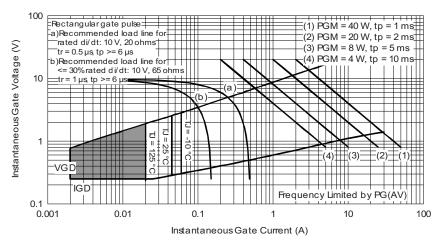
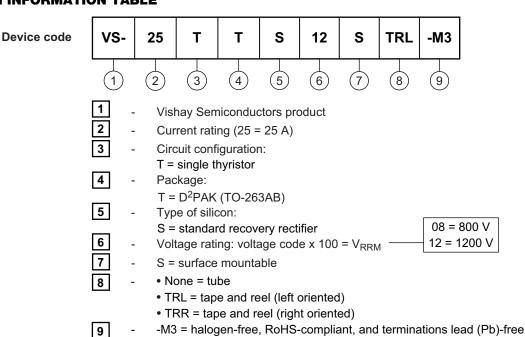


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

#### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-25TTS08S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS08STRR-M3	800	800	13" diameter reel						
VS-25TTS08STRL-M3	800	800	13" diameter reel						
VS-25TTS12S-M3	50	1000	Antistatic plastic tubes						
VS-25TTS12STRR-M3	800	800	13" diameter reel						
VS-25TTS12STRL-M3	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?96164</u>					
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				



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### D<sup>2</sup>PAK

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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